

Superdiffusive Conduction: AC Conductivity with Correlated Noise

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Abstract

We present evidence of the existence of a superdiffusive regime in systems with correlated disorder for which localization is suppressed. An expression for anomalous electrical conductivity at low frequencies is found by using a generalized Langevin equation whose memory function accounts for the interactions between the carriers. New mechanisms inducing a superdiffusive conductivity are discussed and experimental possibilities for observing that phenomenon in nanotubes and superlattices are presented.

One of the most fundamental quantities in transport theory is electrical conductivity whose understanding has permanently represented a challenge for most of the last century. Discoveries of new aspects of this property have always been accompanied by technological innovation. Since finite conductivity is the consequence of the presence of one or more scattering mechanisms, most of the observed conductivity phenomena have always been obtained for diffusive or subdiffusive propagation of the charge carriers. The subdiffusive regime occurs in many different disordered materials such as ion conducting materials or glassy plastics. Measurements of the AC conductivity as a function of the frequency reveal the existence of universal behavior of this quantity whose origin seems to be the only feature shared by those systems: the presence of disorder [1].

The presence of correlated disorder may introduce drastic changes in the transport properties of a system by originating a superdiffusive behavior of the

charge carriers. This behavior can be observed e.g. in the quantum Heisenberg chain [2] where one can find the existence of both a superdiffusive regime emerging at weak correlations and a ballistic regime resulting from strong correlations. A similar result was obtained for a disordered chain [3]. It has been proved as well that the Anderson model with long-range correlated diagonal disorder displays a finite phase of extended states in the middle of the band of allowed energies [4,5]. Moreover, the suppression of Anderson localization has recently been confirmed experimentally in semiconductor superlattices with intentional correlated disorder [6]. Quasi-ballistic and ballistic conduction at room temperature has also recently been observed in carbon nanotubes [7].

The aim of this Letter is to propose a general scenario to describe the conduction mechanism in disordered materials valid for both correlated and uncorrelated disorder. The result can be expressed by a simple equation for the variation of the conductivity as function of the frequency at low frequencies. We show that subdiffusive conductivity increases with the frequency while superdiffusive conductivity decreases. The result is general and independent from a particular microscopic mechanism.

In the linear regime, transport properties can be determined through the knowledge of AC conductivity $\sigma(\omega)$. The first proposed model for AC conductivity, the Drude model, goes back more than a century. In spite of great progress in the field, and the discovery of many forms of universal behavior [1] no general model accounting for the main characteristics of complex disordered systems has been set forth. Although a general relation for $\sigma(\omega)$ is not available, some basic relations involving that quantity established long ago still remain valid. The frequency-dependent diffusion coefficient $D(\omega)$ is related to the conductivity through the expression

$$\sigma(\omega) = \frac{ne^2}{k_B T} D(\omega); \quad (1)$$

where, e is carrier charge, n the carrier density and T is temperature and k_B is the Boltzmann constant. The above equation is a form of the fluctuation-dissipation theorem. The frequency dependent diffusion coefficient is defined as

$$D(\omega) = \int_0^\infty C_v(t) \exp(i\omega t) dt; \quad (2)$$

where $C_v(t) = \langle v(0)v(t) \rangle$ is the velocity correlation function of the carriers and the brackets $\langle \dots \rangle$ indicate ensemble average. Our aim here is to describe the interactions responsible for this behavior using a generalized Langevin equation (GLE) which makes the dependence more explicit and may display superdiffusion as well as normal diffusion and subdiffusion. Our starting point is that it does not matter which way $C_v(t)$ is determined once established, the diffusion and conductivity can be found. In general, complex materials present

a non-Ohmic behavior in the conductivity, and this effect is equivalent to the presence of memory, or a non-Markovian behavior [8,10,12].

Conductivity of complex materials presents in general a non-Ohmic behavior related to the presence of memory effects in the system. These effects have been successfully analyzed in many Non-Markovian systems by means of the GLE. In our case, this equation is given by [8,10,12]

$$m \frac{dv(t)}{dt} = -m \int_0^t (t-t')v(t') dt' + F(t); \quad (3)$$

where $\gamma(t)$ is the memory kernel and $F(t)$ is a stochastic noise subject to the conditions $\langle F(t) \rangle = 0$, $\langle F(t)F(0) \rangle = 0$ and

$$\langle F(t)F(0) \rangle = m k_B T \gamma(t); \quad (4)$$

where m is the effective mass of the carriers. This last equation constitutes the formulation of the fluctuation-dissipation theorem.

The memory function $\gamma(t)$ can be directly defined as

$$\gamma(t) = \int_0^\infty \gamma_n(\omega) \cos(\omega t) d\omega; \quad (5)$$

where $\gamma_n(\omega)$ is the noise density of states or spectral density. Our aim here is to use Eq. (3) to analyze the existence of a superdiffusion regime in conduction by computing the correlation function and from there, the diffusion coefficient and the corresponding conductivity according to formulae (1).

An equation for $C_v(t)$ can readily be obtained from Eq. (3) and the properties of the stochastic force as [10]

$$\frac{dC_v(t)}{dt} = - \int_0^t (t-t')C_v(t') dt'; \quad (6)$$

which can be solved, by means of the Laplace transform yields

$$\tilde{C}_v(z) = \frac{C_v(0)}{z + \tilde{\gamma}(z)}; \quad (7)$$

where $\tilde{C}_v(z)$ and $\tilde{\gamma}(z)$ are the correlation function and memory kernel Laplace transforms. In view of Eq. (7), Eq. (1) can also be expressed as

$$\sigma(z) = \frac{ne^2}{k_B T} \frac{C_v(0)}{z + \tilde{\gamma}(z)}; \quad (8)$$

in Laplace (z) rather than Fourier space (ω). This is our final form for the conductivity given in terms of the memory function and the correlation at the

initial time. For systems where the equipartition theorem holds, one expects that $C_v(0) = k_B T/m$; and the conductivity becomes temperature independent. This feature has never been observed for disordered materials; therefore, the only explanation of this behavior is that equipartition is not fulfilled. It has been shown that for glassy materials the fluctuation-dissipation theorem may fail [11] since the system explores continuously metastable states never reaching true thermalequilibrium. The same expression of the theorem holds in some nonequilibrium situations if one replaces the temperature for an effective temperature [11,12]. The failure of the fluctuation-dissipation relation has also been shown in systems undergoing ballistic motion [12]. In this situation the systems acquire an effective temperature $T_{eff} \neq T$. This effective temperature is a signature of metastability and has been observed in many instances [12].

The conductivity is in view of relation (1) influenced by the nature of the diffusion process through the value of the memory function. Different diffusion regimes can be identified from the asymptotic behavior of the mean square displacement

$$\lim_{t \rightarrow 1} \langle x^2(t) \rangle \sim t^\alpha : \quad (9)$$

This result follows from the GLE with the asymptotic expression for the memory function $\lim_{z \rightarrow 0} \tilde{\gamma}(z) = \tau^{-1} z^{-\alpha}$, where τ is a relaxation time. The diffusion exponent α is connected with β through $\alpha = \beta + 1$ [10]. Consequently, subdiffusion occurs for $-1 < \beta < 0$, normal diffusion for $\beta = 0$, and superdiffusion for $0 < \beta < 1$. For $\beta \leq -1$ the fluctuation-dissipation theorem fails [12]. Our result (8) explains the statement in Refs. [13,1] that at small frequencies $e(z)$ is an increasing function of z for subdiffusive propagation only. From Eq. (8) and the asymptotic value of the memory function given previously, one obtains

$$\frac{de(z)}{dz} = \frac{1 + \tau^{-1} z^{-\alpha}}{(z + \tau^{-1} z^{-\alpha})^2} : \quad (10)$$

Consequently, for frequencies $z < \tau^{-1}$, the derivative will be positive for subdiffusion and normal diffusion, $-1 < \beta \leq 0$, and it will be negative for superdiffusion, $0 < \beta < 1$. The value for the second derivative of the conductivity

$$\lim_{z \rightarrow 0} \frac{d^2 e(z)}{dz^2} \sim -\frac{(\alpha + 1)}{(z)^{\alpha+2}} \quad (11)$$

indicates that the curvature of the function $e(z)$ depends on α and therefore predicts a different behavior of the conductivity in the diffusion regimes discussed. The frequency-dependent conductivity can be inferred from Eq. (10) for small z , yielding

$$\frac{d \ln(e(z))}{d \ln(z)} \sim -\alpha : \quad (12)$$

Note that the previously obtained relations hold regardless of the model used. By simply measuring the real part of the AC conductivity $\sigma'(\omega)$ as a function of the frequency ω , we can obtain information about the diffusive process and the density of states, if the dimensionality of the system is known. If diffusion takes place in a medium of dimensionality d , or in a fractal of fractal dimension d_f , the diffusion coefficient scales as [14]

$$D(\omega) \propto \omega^{d_f - 1}; \quad (13)$$

Theoretical studies have been performed in percolative clusters, as well as experiments on material such as ionic conductive glass or amorphous semiconductors, see [1,15], for reviews. Those processes have $\alpha < 0$, and are subdiffusive. Recent theoretical [4,2,5], and experimental work [6,7], may support our assumption of superdiffusive AC conductivity.

Between normal diffusion and ballistic propagation, i.e., $0 < \alpha < 1$, we may have many possibilities for superdiffusive mechanism, some of which have been discussed for nanotubes and superlattices. The decrease of AC conductivity as a function of the frequency is the main point we propose for experimental observation. Note that the possibility of motion beyond ballistic, $\alpha > 1$, is very rare. However, if they do exist, they violate the fluctuation-dissipation theorem [12], and probably will not be described by linear response theory.

Now we start to look for the possibility of superdiffusive or even ballistic motion in some disorder-correlated system. Adam et al. [16] investigated Bloch oscillations in a one-dimensional lattice with long-range correlated diagonal disorder. For their system, the Schrödinger equation for the Wannier amplitude is

$$i \frac{d}{dt} \psi_n = (\epsilon_n - F) \psi_n - \psi_{n+1} - \psi_{n-1}; \quad (14)$$

where F is an external electrical field, and the stochastically fluctuating energies are

$$\epsilon_n = \sum_{k=1}^{N/2} k^2 \cos(kn - \phi_k); \quad (15)$$

and ϕ_k are random phases in the interval $[0, 2\pi]$. For $N > 2$, this model supports delocalized states with a clear signature of Bloch oscillations. Recent studies [2] for the quantum Heisenberg chain with N sites, and exchange similar to the energies above, present quite similar behavior. For example, the spin wave function localized at the origin at $t = 0$, will present a superdiffusive motion with $\alpha = 3/2$ for the weak coupling, $0 < \alpha < 1$. For strong coupling $\alpha > 1$, the diffusion is ballistic. It has been proved as well that the Anderson model with long-range correlated diagonal disorder displays a finite phase of extended states in the middle of the band of allowed energies [4,5]. Ballistic diffusion have

been proposed as well for ratchet devices using a thermal broadband noise, with the elimination of the lower modes [17]. Moreover, the suppression of Anderson localization was confirmed experimentally in semiconductor superlattices with intentional correlated disorder [6]. This behavior seems to be universal insofar as a correlated disorder as the one above can be defined. The correlation disorder is of course, the main scattering mechanism which will be in charge of conduction. Some realistic simulations would be helpful to find the best conditions to produce that material. Despite the difficulties involved, experiments similar to those by Bellani et al. [6], may suggest that the stage is now set for superdiffusive conductors.

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